

Product Summary

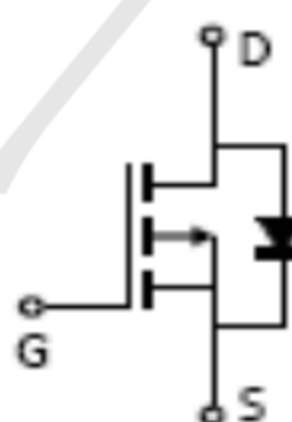
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-3.0A < 88m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-2.6A < 108m\Omega$

Application

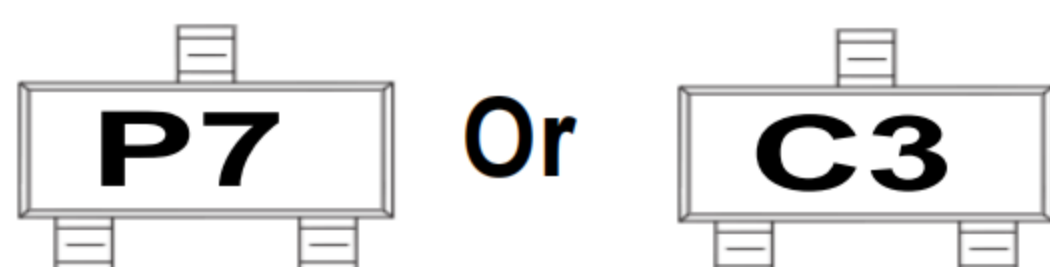
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration

SOT-23



Marking:



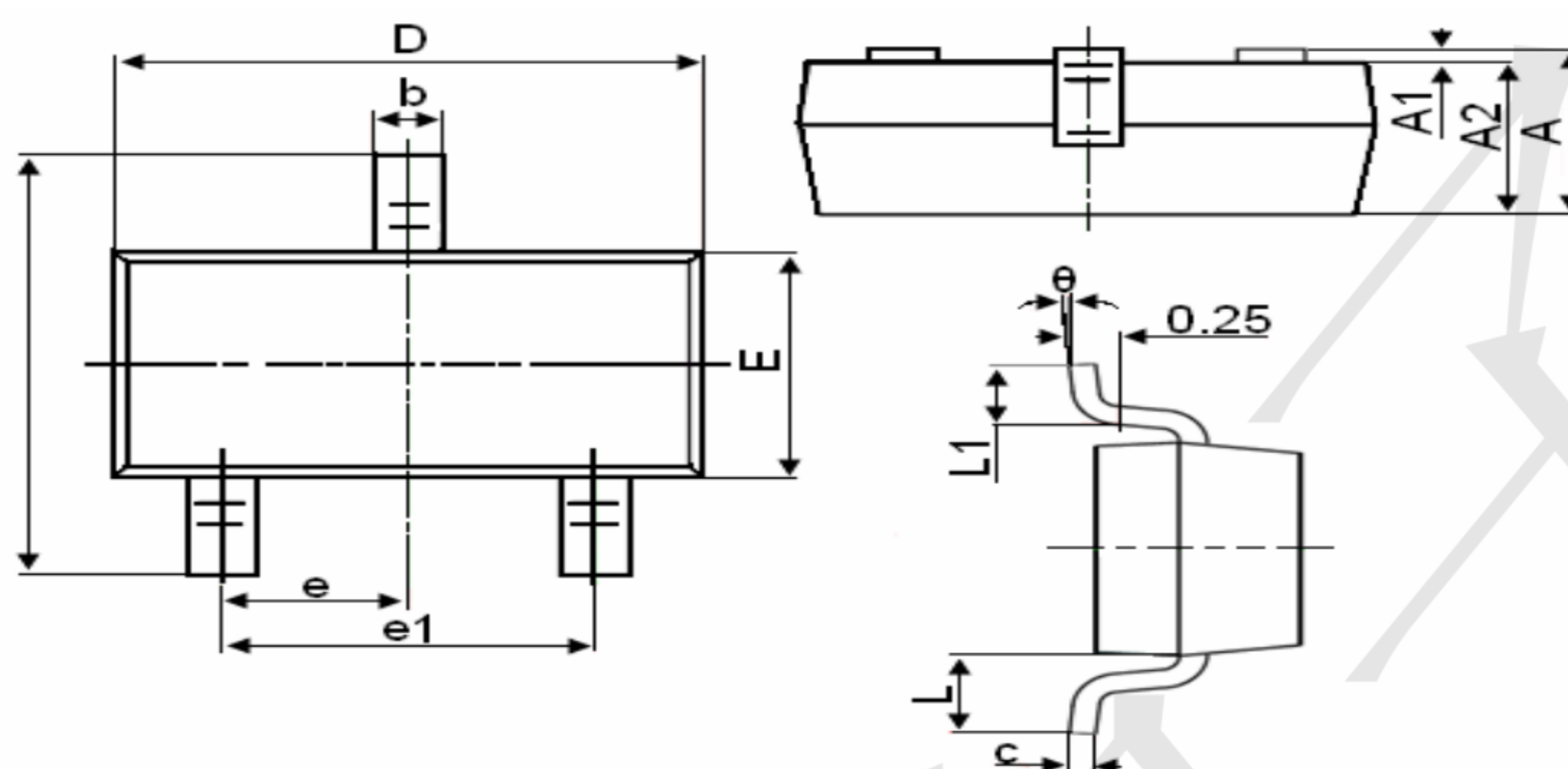
Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	<u>±</u> 20	
Continuous Drain Current		I_D	-3.0	A
Pulsed Drain Current (Note 4)		I_{DM}	-12.4	
Power Dissipation	$T_a=25^{\circ}\text{C}$	P_D	1.25	W
	Derate above 25°C		10	mW/ $^{\circ}\text{C}$
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^{\circ}\text{C}$
Typical Thermal Resistance		$R_{\theta JA}$	100	$^{\circ}\text{C/W}$
- Junction to Ambient (Note 3)				

Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

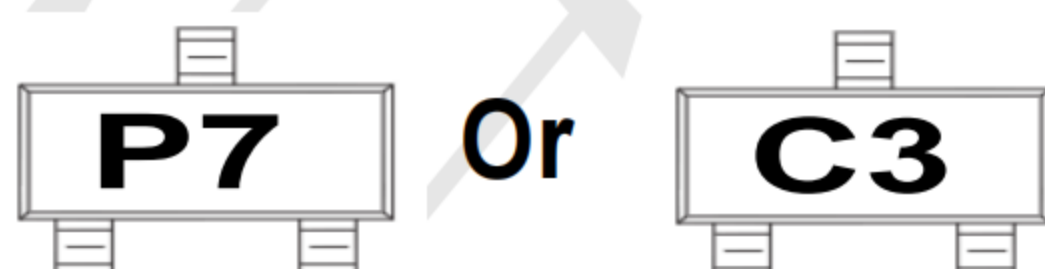
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-3.1A$	-		95	mΩ
		$V_{GS}=-4.5V, I_D=-1.2A$	-		158	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	uA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic (Note 5)						
Total Gate Charge	Q_g	$V_{DS}=-20V, I_D=-3.1A,$ $V_{GS}=-4.5V$ (Note 1,2)	-	6	-	nC
Gate-Source Charge	Q_{gs}		-	1.6	-	
Gate-Drain Charge	Q_{gd}		-	2.3	-	
Input Capacitance	C_{iss}	$V_{DS}=-20V, V_{GS}=0V,$ $f=1.0MHz$	-	505	-	pF
Output Capacitance	C_{oss}		-	48	-	
Reverse Transfer Capacitance	C_{rss}		-	33	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=-20V, I_D=-2.5A,$ $V_{GS}=-10V,$ $R_G=1\Omega$ (Note 1,2)	-	6	-	ns
Turn-On Rise Time	t_r		-	35	-	
Turn-Off Delay Time	$t_{d(off)}$		-	18	-	
Turn-Off Fall Time	t_f		-	10	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	-1.0	A
Diode Forward Voltage	V_{SD}	$I_S=-1.0A, V_{GS}=0V$	-	-0.82	-1.2	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_S=-2.5A$	-	13	-	ns
Reverse Recovery Charge	Q_{rr}	$dI_F/dt=100A/us$	-	8.7	-	nC

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Marking:



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